nascom

Nascom RAM B 4Mhz / 48K Dynamic Memory Card

Constructional and Functional Specification
DOCUMENTATION

NM Part No. 024-300

Issue 3

The Nascom Microcomputers Division of Lucas Logic Limited reserves the right to amend/delete any specification in this brochure in accordance with future developments.

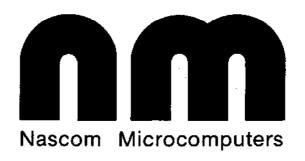
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NASCOM type B RAM board: PCB modification

On issue 3 board, immediately adjacent to LK2, there will be found a wide track running along the edge of the board at right angles to the edge connector.

If only one through-plated hole is provided to connect the wide track to its counterpart on the other side of the board it is recommended that a piece of wire be soldered through the hole to provide greater current capacity.

Introduction

The RAM B is a Dynamic random access memory board. The memory may be configured to have a memory capacity of 16k, 32K or 48K bytes of user RAM. This on-board memory expandability is made possible by population options of either eight, sixteen or twenty-four MK4116 (16,384x1 MOS dynamic RAM) memories. The RAM B provides options for positioning the decoded memory space to start on any 4K address boundary. The RAM B also includes logic for a "Page mode operation" which permits up to four, fully populated, RAM B boards to be used in one system (192K in total).

This Manual contains all the information necessary to build, test and use your 4Mhz - 48K Dynamic RAM card. A separate Manual has been produced to cover the additional construction and use of the Page mode and Write protect upgrade kit (part no 024-110).

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	Introduction for construction Component Check list Suggested order of construction Component placement Memory test software Specifications Circuit description Suggested memory map Memory array supply links Page mode links Addressing link options References

Construction

- 1. Do not begin construction now. Read through all the documentation at least twice before starting in order to ensure that no fundamental and expensive errors are made.
- 2. Do not leave the MK4116 Dynamic RAM integrated circuits out of their antistatic packing. (see Nascom 1 or 2 Manual for MOS handling instructions).
- 3. Keep the box in which the RAM card was delivered in case it should have to be returned for repair.
- 4. Do not attempt to use too large a soldering iron. Use an earthed 15 to 25 watt soldering iron equipped with a suitably small bit. Use 22 Swg resin-cored solder.
- 5. Fit all components in the board on the same side as the printed information.
- 6. Be certain to fit all integrated circuits and tantalum bead capacitors in the correct locations and the correct way round.
- 7. Be certain to connect the power supplies to the Bus the correct way round. (See Nasbus functional specification, part No. 003-310).
- 8. Do not attempt to remove or plug in integrated circuits on the board or perform any soldering while the power supply is switched on.
- 9. If any difficulty is experienced when plugging an IC into its socket do not use extreme force. If in doubt remove the IC; check that the pins are straight and parallel and start again. An IC insertion too! may be found useful. Note that all ICs are manufactured with the leads spread apart by a few degrees to suit mechanised handling equipment. They can be bent parallel with care using small pliers or one row at a time by pressing down sideways on a flat surface. There should be no bend in the leads and they should be at right angles to the body.
- 10. Before switching on any power supplies, hold the board up against a powerful lamp and inspect both sides with a magnifying glass for solder splashes, unsoldered joints, incorrectly orientated components and bent IC pins. (To check for the latter look at all ICs end on). TAKE TIME OVER THIS.

11. The following tools are needed:-

- (a) Long nose pliers
- (b) Side cutters
- (c) 15 to 25 watt soldering iron(d) A damp sponge or cloth to keep iron bit clean
- (e) A powerful light source
- (f) A magnifying glass for inspecting the PCB
- (g) A multimeter not necessary, but useful to check supplies

COMPONENT LIST

No.	Part No.	Qty	Desci	ription	Circuit ref.
INTE	GRATED CI	RCUITS			
01	501-244	4	74LS244	Octal Tri-state buffer	· 1025 to 28
02	501-075	i	74LS75	Quad latch	IC29
	501-156	2	74LS156		(C30 & 31
04	502-074	ī	74874	Schottky dual D-type	
04	302 074	-	74071	flip-flop	1032
05	503-157	2	74157	TTL Quad 2 to 1	
0,5	305 25.	_		multiplexer	IC33 & 34
06	501-020	1	74LS20	Dual 4 input Nand gate	e 1C35
07	501-008	2	74LS08	Quad 2 input And gate	IC36 & 41
0.8	501-032	2	74LS32	Quad 2 input Or gate	1C37 & 38
09	503-006	2 2 1 1	7406	TTL 0'c Hex inverter	1 C39
10	501-279	ī	74LS279	Quad reset/set latch	1C40
11	501-004	$\overline{1}$	74LS04	Hex inverter	IC46
12	601-900	ī	54-018	Polara 150ns active	
	001 300	-	• •	delay line	1C47
MEM	ORY				
	024-100	8	MK4116	Dynamic RAM / 16K kit	IC1 to 8
	024-101	16	MK4116	Dynamic RAM / 32K kit	IC1 to 16
	024-102	24	MK4116	Dynamic RAM / 48K kit	IC1 to 24
				·	•
RES	ISTORS			_	- n-
14	614-100	1	899-3-R	33 33R resistor pack	RP1
15		1	899-3-R	47 47R resistor pack	RP2
16	614-101	1	898-1-R	4.7K 4K7 resistor pack	RP4
17	614-102	1 1	899-3-R	4.7K 4K7 resistor pack	RP5
	510-272	6	2K7 .25	watt red - violet - re	d R1 to 6
	510-102	4	1K .25	watt brown - black - r	ed R7,8,9,14
20	510-221	4	220R.25		R10 to 13
- -					

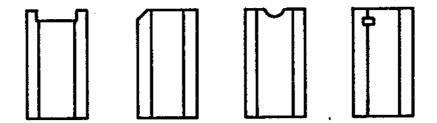
	\$TORS Cont 510-220	1	22R .25watt red - red - black R15	
22	CITORS 609-127 609-110		10uF Tantalum bead 25v C78 2uF2 Tantalum bead 35v C74 t	
			100n Ceramic disc C1 t 10n Ceramic disc C49 t 71,72	0 48 0 69
26 !	520-330	2	33pf Ceramic disc C70 &	
27 28	705-102	31	20 pin .3 inch DIL 16 pin .3 inch DIL 14 pin .3 inch DIL	
30	ELLANEOUS 705-113 710-100 024-200	1 1 1	20 pin header plug .3 inch DIL SKT 1 77 way Nasbus connector PL 1 RAM B PCB	

SUGGESTED ORDER OF CONSTRUCTION

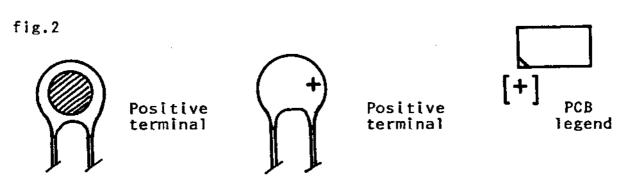
- 1. Unpack the kit and check the contents against the parts list. Return the memory ICs to their antistatic packing immediately after checking. Inspect the printed circuit board (PCB) for any signs of damage.
- 2. RESISTORS Preform the leads of the 15 resistors to a seperation of 1/2inch (12.7mm). Some resistors may be supplied already formed. Insert the resistors into the card. Components may be held in place after insertion by bending the leads about 40 degrees in the opposite direction. Solder the resistors.
- 3. IC SOCKETS Check to see that all the IC sockets do not have their pins bent or missing. During insertion take care not to bend any pins. When soldering the IC sockets it may be a good idea to solder only two pins on opposite corners to begin with. Then turn the board over again and check that the sockets are flat on the board, straight and also correctly oriented. See figure 1 for typical socket orientation marks. Any necessary alterations may now be carried out with ease, as only two pins are soldered.



fig.1b Typical orientation marks viewed from above, pins facing away from you. Pin 1 is the top left hand corner in each case.



4. CAPACITORS Insert and solder:- (1) The 48, 100n ceramic capacitors, located near the memory array which are C1 to C48. (2) The 24, 10n ceramic capacitors. (3) The 2, 33pf ceramic capacitors which are C70 and C79. (4) And finally the tantalum capacitors. These are electrolytic capacitors and as such must be correctly orientated (see fig.2), C78 is 10uf. C74 to C76 and C80 to C82 are 2.2uf.



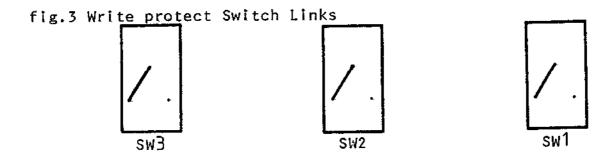
- 5. Using offcuts from the resistors or capacitors, solder in position the test points marked with a square on the PCB. The GND (0v) test point is located near the 77 way edge connector. The remaining test points are located near the opposite edge of the PCB. These test points are, from left to right WR EN, RD EN, MUX, WR2, WR1, RASO, CAS, RAS2, WR0 and RAS1. Crop the leads on the component side of the board leaving about 3/8ths inch or enough lead to enable test hooks to be hooked onto them. Crop the leads on the circuit side.
- 6. LINKS If the "Page mode and write protect upgrade kit" is not installed and memory type MK4116 is used wire the links as shown overleaf:-

LK1 c to 2 LK2 c to 2 LK3 c to 2 LK5 c to 1 LK6 c to 2 LK7 leave out

If the upgrade kit is installed and memory type MK4116 is used wire the links as follows:-

LK1 c to 2 LK2 c to 2 LK3 c to 2 LK5 c to 2 LK6 c to 1 LK7 wire in link

Please note that incorrect positioning of LK1,2 and 3 may result in the memory being damaged. For further information on link options refer to section 3-4 of this manual. Finally, a link should be inserted in each of the three switch pads (SW1 to 3) when the upgrade kit is not used, as illustrated below.

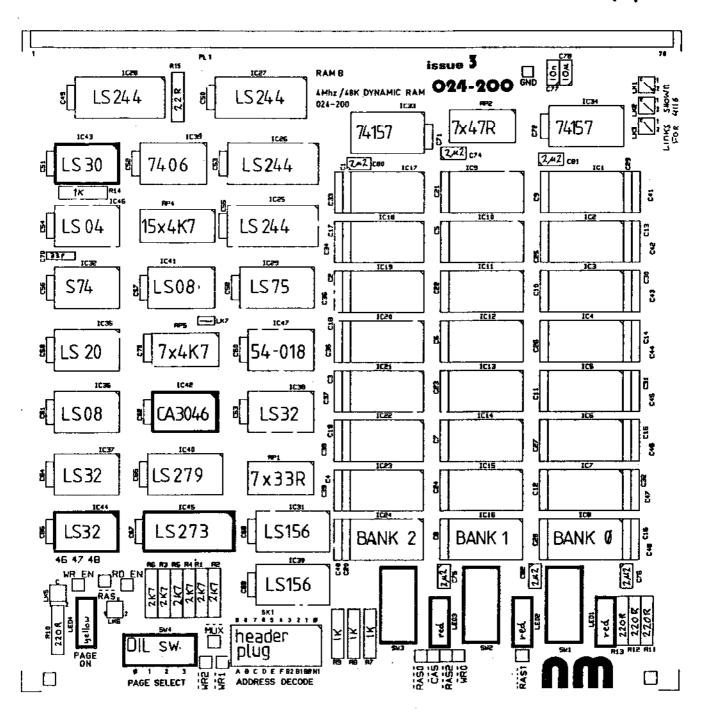


6. ADDRESS DECODE Insert the 20 pin header plug into SK1. One corner of the plug has a notch in it, this is pin 1. It is suggested that the address decode links are soldered onto the header while inserted into SK1. This will maintain the pin alignment while the pins are hot. Refer to section 3-5 of this manual and wire in position the decode links on the header plug.

7. INTEGRATED CIRCUITS insert the resistor packs and ICs in the following sequence:-

```
RP1....899-3~R33
(1)
    RP2.....899-3-R47
(2)
    RP4........898-3-R4.7
(3)
    RP5.....899-3-R4.7K
(4)
    IC25 to 28.....74LS244
(5)
    IC33 & 34.....74157
(6)
    1039..........7406
(7)
    IC46...........74LS04
(8)
    1C32.....74LS74
(10) 1C36 & 41.....74LS08
(11) IC29.........74LS75
(12) [C35......74LS20
(13) 1047......54-018
(14) 1C37 & 38.....74LS32
(15) 1C40......74LS279
(16) | C30 & 31.....74LS156
(17) IC1 to 8......MK4116 for 16K bytes
                  of memory
    IC1 to 16.....MK4116 for 32K bytes
                  of memory
    IC1 to 24.....MK4116 for 48k bytes
                  of memory
```

- ** IC 47 (the delay line) has pin 1 indicated by a white dot. When completed, check that ICs are correctly orientated and in the right place.
- 8. Take a final look at the card and check that there are no unsoldered pins or solder bridges anywhere.
- 9. When satisfied everything is correct, plug the board into the system. Power up the system and, if a multimeter is available, check the supply voltages. Check Nascom 1 or 2 for Normal operation.
- 10. Enter the machine code "Memory test" program which may be found in section 2 page 1.



SECTION 2

1. MEMORY TEST PROGRAM.

This program is designed to run under Nas-sys on a Nascom 1 or 2. The program is split into two halves, part 1 executes three tests giving the following error letter if the condition is not met:-

A - Location not set to zero

B - Walking bit test

C - location not set to FF

Part two of the program loads a jump instruction into each location and then executes it, moving the jump through the memory as it goes. If the program "crashes" because of a fault in memory the screen will hold the last address, or if this is cleared or corrupted locations OD49 & OD4A will still contain it. The program will loop till a system reset or fault occurs.

Execute 0080 ssss eeee . Where ssss is the first location and eeee is the last location of memory to be tested.

ZEAP Z80 Assembler - Source Listing

0290	; NA	S-SYS		i		
OCOE 0300	ARG2	EQU	#OCOE			
0C10 0310	ARG3	EQU	#0C10			
0C29 0320	CURSOR	EQU	#0C29			
0018 0330	SCAL	EQU	#18			
0028 0340	PRS	EQU	#28			
0030 0350	ROUT	EQU	#30			
0066 0360	TBCD3	EQU	#66			
0068 0370	B2HEX	EQU	#68			
0069 0380	SPACE	EQU	#69			
006A 0390	CRLF	EQU	#6A			
000C 0400	CS	EQU	#0C			
000D 0410	CR	EQU	#0D			
0420	;					
0430	;					
0440	;					
0080 0450		ORG	#0¢80			
0C80 EF 0460		RST	PRS			
0C81 0C 0470		DEFB	CS,0			
0C83 EF 0480	LOOP	RST	PRS		DART	4,
0C84 4D 0490		DEFM	/MEMORY	TEST	PART	1/
0C96 0D 0500		DEFB	CR _x 0			

0C98 0C9B	2A100C	0510 0520	LD XOR	HL,(ARG3)	;FINISH ADDR
	ED5B0E0C		LD		;START ADDR
	ED550E0C	0540	SBC		;CALC COUNT
OCA 2		0550	PUSH		COUNT ON STACK
OCA2		0560	LD	B _c H	,000 m 0 m 0 m 0 m
OCA4		0570	LD	C.L	;AND IN BC
	2A0E0C	0580	LD	HL (ARG2)	
OCAS		0590	PUSH		START ADDR ON STACK
OCA9		0600	LD	D _c H	, 2, , , , , , , , , , , , , , , , , ,
OCAA		0610	LD	E_L	; AND DE
OCAB		0620	INC	DÉ	READY FOR LDIR
	3600	0630	LD	(HL) ₂ 0	; ZERO THE 1st LOCATION
	EDB0	0640	LDIR	• • • • • • • • • • • • • • • • • • •	AND COPY IT THROUGH
0CB0		0650	POP	HL	START ADDR BACK
OCB1		0660	POP	BC	;AND COUNT
0001	01	0670			CHECK FOR ZERO'S
0CB2	1600	0680 ZCHK	LD	D, 0	CLEAR ERROR FLAG
0CB4		0690	XOR	A	CLEAR A
OCB5		0700	CP	(HL)	MEMORY SHOULD BE ZERO
	3E41	0710	LD	A, "A	;LOAD ERROR LETTER IN
0000	2212	V. 2V			CASE
0CB8	C4390D	0720	CALL	NZ, ERR	;FAULT A IF NON-ZERO
		0730;			-WALKING BIT TEST
OCBB	3E01	0740	LD		
OCBD		0750 WALK	LD	(HL),A	; PUT IT IN MEMORY
OCBE		0760	CP		;DID IT GET THERE
OCBF		0770		AF	;SAVE BIT PATTERN
	3E42	0780	LD	A,"B	;LOAD ERROR LETTER IN
			•		CASE
OCC2	C4390D	0790	CALL	NZ,ERR	FAULT B IF WALK FAILS
0005	F1	0800	POP	AF	;BIT PATTERN AND FLAGS
0006	2003	0810	JR	NZZAŁFF	; IF IT FAILED DO NEXT
					TEST
0008	_	0820	RLA		;WALK BIT ACROSS
0009	30F2	0830	JR	NC,WALK	;UNTIL IT REACHES
					CARRY
		0840;			-LOAD FF TEST
	3EFF	0850 ALFF	LD	A,#FF	
OCCD		0860	LD	(HL),A	SIS IT AFT TUESE
OCCE		0870			;DID IT GET THERE
0CCF	3E43	0880	LD	A,"C	;LOAD ERROR LETTER IN
				W7 588	CASE
	C4390D	0890		NZERR	FAULT C FF NOT LOADED
OCD4		0900	LD	A _c D	GET ERROR FLAG
OCD5	B7	0910	OR	A	;NON-ZERO IF ERROR
00=0	01.1.555	0000	0.61.1	Mar Reguet Ki	OCCURED
-	C4460D	0920		NZ_NEWL1	;STEP ON TO NEXT
ocD9	EDA0	0930	LDI		LOCATION
0000	E 4 D 6 6 6	0.01:0	LD	DE ZCUV	;LOOP TILL END REACHED
UCDB	EAB20C	0940	JP	PE,ZCHK	SCOOL LIFE BUD KENOUED

```
-----TWO
               0950;-----
              0960
                           RST PRS
OCDE EF
                           DEFB CR
OCDF OD
              0970
                           DEFM / PART 2 OP-CODE FETCH TEST/
OCEO 50
              0980
              0990
                           DEFB CR_0
OCFA OD
                                 HL_(ARG3)
                           LD
OCFC 2A100C
              1000
                           XOR
              1010
                                 А
OCFF AF
                                 DE, (ARG2)
                           LD
ODOO ED5B0E0C 1020
                                          ;CALC COUNT
                            SBC
                                 HL,DE
              1030
0D04 ED52
                            LD
                                 B,H
0D06 44
              1040
                           LD
                                 C,L
                                           COUNT IN BC
0D07 4D
              1050
                                 BC
0D08 0B
               1060
                            DEC
                                           ; MAKE ROOM FOR JP
               1070
                            DEC
                                 BC
0D09 0B
                            ΕX
                                 DE,HL
                                           ;HL=ARG2
               1080
ODOA EB
               1090 OPLOOP PUSH HL
                                           START ADDR
ODOB E5
                                 A,#C3
                            LD
ODOC 3EC3
              1100
                                 (HL)_A
ODOE 77
                            LD
               1110
                                           ; PUT JP IN MEMORY
                            INC
               1120
                                 ΗL
ODOF 23
                                 DE, RETURN
                            LD
OD10 11270D
               1130
                            LD
                                 (HL),E
0D13 73
               1140
               1150
                            1 NC
                                 HL
0D14 23
                                           ;FOLLOWED BY ADDRESS
                            LD
                                 (HL)_D
0D15 72
               1160
                                           GET START ADDR BACK
                            POP
                                 HL
               1170
0D16 E1
                            LD DE, (CURSOR); GET CURRENT CURSOR
OD17 ED5B290C 1180
                                           ;SAVE COUNT
               1190
                            PUSH BC
OD1B C5
                            RST
                                 SCAL
ODIC DF
               1200
                            DEFB TBCD3
                                           ; PRINT CURRENT ADDR
0D1D 66
               1210
                            LD (STORE), HL ; SAVE ADDR WE MAY BOMB
OD1E 22490D
               1220
                            LD (CURSOR), DE; REPLACE OLD CURSOR
OD21 ED53290C 1230
                                           GET COUNT BACK
                            POP
                                 BC
               1240
0D25 C1
                                           JUMP TO TEST RAM
                                 (HL)
                            JP
               1250
0D26 E9
                                           ; RETURN HERE HOPFULLY
               1260 RETURN LD!
0D27 EDA0
                                 PE,OPLOOP; LOOP TILL DONE
                            JΡ
OD29 EAOBOD
               1270
                            RST
                                 PRS
OD2C EF
               1280
                            DEFM /LOOPING/
               1290
0D2D 4C
                            DEFB CR.O
               1300
0D34 0D
                            JP
                                 LOOP
0D36 C3830C
               1310
                                -----ERROR ROUTINE
               1320;----
                            PUSH AF
                                           ;SAVE FLAGS
               1330 ERR
0D39 F5
                                           ;OUTPUT ERROR LETTER
                            RST
                                 ROUT
0D3A F7
               1340
                            RST
                                 SCAL
OD3B DF
               1350
                                           :AND SPACE
                            DEFB SPACE
0D3C 69
               1360
                                           ;SAVE COUNT
                            PUSH BC
0D3D C5
               1370
                                 SCAL
                            RST
ODSE DF
               1380
                                           ;OUPUT ADDR
                            DEFB TBCD3
               1390
0D3F 66
                            P0?
                                 BC
0D40 C1
               1400
0D41 DF
               1410
                            RST
                                 SCAL
                            DEFB SPACE
               1420
OD42 69
                                           ;SET ERROR FLAG
                            INC
                                 D
0D43 14
               1430
```

0D44	F 1	1440		-	AF			
0D45 0D46		1450 1460	NEWLIN	RET RST	SCAL			
0D47	6A	1470		DEFB				
0D48 0002	C 9	1480 1490	STORE	RET DEFS	2	;SPACE	FOR	ADDR
					λ			

Memory test object code listing

```
EF OC 00 EF 4D 45 4D 4F 52 59 20 54 45 53 54 20
0080
      50 41 52 54 20 31 0D 00 2A 10 0C AF ED 5B 0E
                                                    0C
0090
      ED 52 E5 44 4D 2A 0E 0C E5 54 5D 13 36 00 ED
OCA0
      E1 C1 16 00 AF BE 3E 41 C4 39 OD 3E 01 77 BE F5
OCB0
      3E 42 C4 39 OD F1 20 03 17 30 F2 3E FF 77 BE 3E
0000
      43 C4 39 OD 7A B7 C4 46 OD ED A0 EA B2 OC EF OD
OCD0
                                          4F 44 45 20
      50 41 52 54 20 32 20 20 4F 50 2D 43
OCEO
      46 45 54 43 48 20 54 45 53 54 0D 00 2A 10 0C AF
0CF0
      ED 5B 0E 0C ED 52 44 4D 0B 0B EB E5 3E C3
0D00
      11 27 0D 73 23 72 E1 ED 5B 29 0C C5 DF 66 22 49
0D10
      OD ED 53 29 OC C1 E9 ED A0 EA OB OD EF 4C 4F 4F
0D20
      50 49 4E 47 0D 00 C3 83 0C F5 F7 DF 69 C5 DF 66
0D30
      C1 DF 69 14 F1 C9 DF 6A C9 00 00 00 00 00 00
0D40
```

Upon execution of the above program the VDU should output the following message if the Memory card is functions correctly.

MEMORY TEST PART 1

PART TWO OPCODE FETCH TEST xxxx (rapidly changing addresses) LOOPING

This message will be repeated until either a fault condition arrises or a system reset is performed.

However if the Memory card is faulty the VDU would output a message similar to the example below;-

MEMORY TEST PART 1
A aaaa B bbbb C cccc
A aaaa B bbbb C cccc
A aaaa
A aaaa B bbbb
A aaaa B bbbb C cccc

PART 2 OPCODE FETCH TEST eeee

Where aaaa is a location in memory that will not set to zero, bbbb will not accept certain data patterns, cccc will not set all bits high & eeee was the last address that did not accept a jump command.

Memory test program copyright c 1980 CC Soft.

SECTION 3

1. SPECIFICATIONS

Memory capacitymax. 48K bytes in 16K increments
Memory cycle time (without wait state)400ns min.
Memory access time (without wait state)150ns max.
Operating temperature
Interface levelsTTL compatible
Supply requirements+12v +/- 5% @ 130mA typ.
(fully populated) +5v +/- 5% @ 300mA typ.
-5v +/- 5% @ 25mA typ.
Physical dimensions8 x 8 inches
Bus structureto Nasbus Issue 4 specification

2. NASBUS MEMORY ASSOCIATED CONTROL SIGNALS

- MREQ Memory request indicates that the address bus holds a valid address for memory read, write or refresh.
- RFSH Refresh indicates that the lower seven bits of the address bus contain a refresh address for dynamic memory.
- RD Read indicates that the CPU wants data from 1/0 or memory.
- WR Write indicates that the data bus holds valid data for memory to store
- RAMDIS RAM disable is an active low signal which disables output from any RAM on the bus. Used to give ROM priority over RAM.
- M.EXT A decoded signal from one of the RAM boards in the system defining which 4K block is used by Nascom 1. Not used by Nascom 2.

DBDR Data bus drive determines the direction of the bidirectional data bus buffers on the buffer card. Low to drive data to the Nascom. Not used by Nascom 2.

The following circuit description should be read in conjunction with the circuit diagrams to be found near the end of this manual.

- 3. ADDRESS and DECODE LOGIC Address lines A0 to All buffered by ICs 27 and 28 (Schottky Schmitt). Buffered address lines A0 to A13 are routed to address switches 1033 where they are switched into the memory array to provide row (A0 to A6) and column (A7 to A13) addresses. The row and column addresses are strobed into the memory by two negative w address strobe (RAS) and column By the use of RAS and CAS the address going clocks called Row address strobe address strobe (CAS). bits are latched into the memory for access to the required memory location. Because the Z80 CPU does not guarantee that the address bus will hold valid information past the rising edge of MREQ on an Op-code fetch, A12 to A15 are latched (1029) each time MREQ is active. This prevents glitches appearing on the RAS lines. Al2 to Al5 are decoded in ICs 30 and 31 to provide select signals for each 4K byte block of memory starting at any 4K boundary. These signals arrive at pins 1 to 16 of SK1. Pin 20 of SK1 provides the M.EXT signal which is necessary to decode the internal addressing of Nascom 1. This signal is not required by Nascom 2. Pins 17,18 and 19 (SK1) are the memory array bank selects. These selects should be commoned to four of the 16 4K decodes. A0 to A7 are also routed to IC43 for Port decoding when "Page-mode" is used.
- 4. MEMORY CONTROL LOGIC MREQ is buffered by IC 27/3 and inverted by IC46/8. The output from IC46/8 is Anded (IC36/11) with the output from the 4Mhz Z80 precharge extender circuit (IC32) and is then inverted by IC46/10 (TP9-RAS). The RAS signal is then Ored in IC37/3/6/8 with the Anded bank decode and Refresh signals. When a memory bank is decoded only one RAS line to the memory array goes low. However, if a memory refresh is being performed, all the RAS inputs to the array will go low. The Active delay line (IC47), whose input is MREQ, goes low at pin 4 (MUX) approximately 60ns after MREQ goes active. All memory timing is referenced to MREQ. The 60ns delay was chosen to allow an adequate margin for the row address hold time. The signal controls the address multiplexers (IC33 & 34). Until now the memory array has been receiving the row addresses (A0 to A6). When MUX goes low the

column addresses (A7 to A13) are then switched to the array address inputs. After a further delay of approximately 30ns the delay line goes low at Pin 11 (CAS). This signal is then Ored in IC37/11 with RFSH. If a refresh is not being performed the memory array will receive CAS. It is necessary to delay CAS from MUX in order to allow the addresses to stabalise after being switched. When CAS is received the memory then latches the column addresses.

- The WR signal is buffered in 1027/7 5. READ and WRITE LOGIC and is then Ored with the output of the card page mode WREN circuitry (TP10). This line is taken to the common terminal of LK5. If page mode is not installed then LK5/C should be connected to LK5/1 (+5v). This will permanently enable write However, if page mode is installed, this link should be connected the other way round (LK5/C to LK5/2). This WREN signal to the page mode circuitry and only when the card is paged in, will WREN be enabled. This signal is active high. The combined WR and WREN signal is then further Ored within the remaining three gates of $1\bar{C}38$ with the memory bank write protect signals from 1C40/4,7 & 9. The outputs of IC38 are taken to the memory array WR inputs via 3 33R resistors within RP1. The WR inputs to the memory array also appear at TP6.7 & 8 where they are marked WR 0 - 2 on the PCB. The write protect switches are supplied with the page mode kit (SW 1-3) so when the card is not used in page mode necessary to install 3 links, one in each of the switch pads; as shown in Fig. 3 Because these write protect inputs are fully buffered, it is possible to have SW 1 - 3 mounted in a remote site not too far away from the card and connected to the pads of each switch. The RD input is buffered in 1039/4 which appears at an input of 1035/8. The other inputs to this gate are MREQ, decode and card RDEN. The output of the gate when active enables the data output buffer IC25 and will bring DBDR low. The memory will output data when addressed only when its write inputs are not active. (For further information on the memory chips, refer to Mostek's data sheet The card RDEN (TP11) signal is similar on the MK4116). the previously mentioned WREN signal. When page mode is not installed, it is necessary to link LK6/C to LK6/2. LK6/C should be linked to LK6/1 if page mode is installed.
- 6. PAGE MODE and write protect upgrade kit. 1C43 decodes the port (port FF) and is Ored with WR in IC44/3. This signal is subsequently Ored with IORQ which is used as a clock to latch data into IC45. The outputs from IC45 will all be low on power-up as the system reset is connected to the master reset input of this IC. Also on power-up, IC40/13 will be high bringing IC44/8 & 11 high. SW4 is a four position dil switch which selects the card page number. If in position 0 as marked

on the PCB, the card will become active on power-up and up until such time as the port status changes. By changing the data of port FF one card can be paged out and another paged into the system. Because of this method of paging possible to enable one card to read only and another to write only; so by allowing the processor to read and write to the address, data will be transferred from one page to another. This illustrates only one of many ways in which the page mode facility can be used. The page on LED (LED4) will be lit up when a page is read enabled. LED1, 2 & 3 will be lit if write protect switch is in its protect position. These LEDs are driven by IC42 which is a five NPN transistor array. The fifth transistor in this package is used to provide Nasbus with an 10/EXT signal. When page mode is not installed, LK7 should not be present. Nasbus lines 46 to 48 are brought onto the card to allow the facilities of the page mode to be extended at a later date.

7. SUGGESTED NASCOM MEMORY MAP

0000 to Ø7FF Existing operating system

0800 to OBFF Existing video RAM

0000 to 007F Existing operating system workspace

0C80 to 0CFF Extended operating system workspace

0D00 to 0F7F Workspace for firmware or workspace for programs

0F80 to 0FFF Usual stack space

1000 to 8FFF General RAM space. Start of general program space

9000 to 9FFF Programmable graphics RAM or general RAM space

9800 to AFFF Colour graphics RAM or general RAM space

B000 to B7FF Extensions to the operating system or extensions to Naspen

B800 to BFFF Naspen or related word processing software

COOO to CFFF Revas or general dissembler software or Colour graphics control software

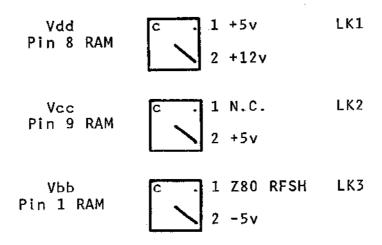
Memory map continued...

D000 to DFFF or general assembler type software or extensions to Basic

E000 to FFFF 8K Basic

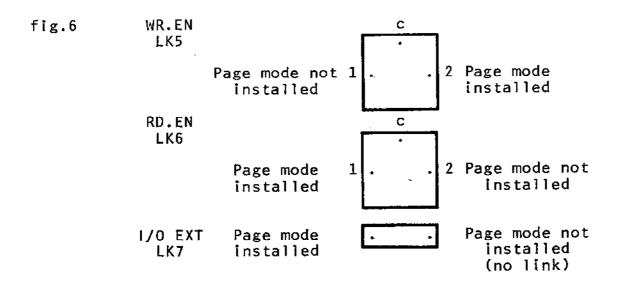
8. MEMORY ARRAY SUPPLY LINKS (LK1 to 3) These three links are provided to enable memories other than type MK4116 to be used on the board. This includes new memories not yet available such as Pseudo-Static devices. If this type of device is used in the future, some makes may require the Z80 refresh signal at pin 1. In this case change LK 3 (c to 1) and remove tantalum capacitors C80, 81 and 82. Check the supply requirements for these devices and change LK1 and 2 where appropriate

fig.5 Links 1 to 3



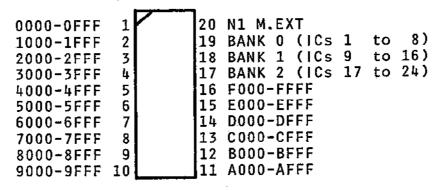
The above links 1 to 3 are shown in the correct position for use with MK4116 Dynamic memory, as supplied with the kit.

9. PAGE MODE LINKS (LK5 to 6)



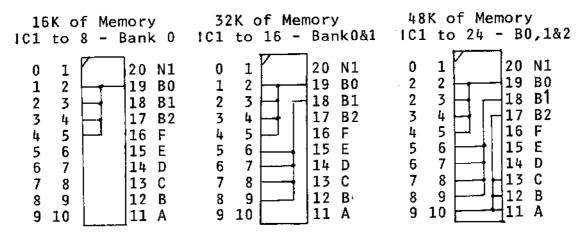
10. ADDRESSING LINK OPTIONS

fig.7 SK1 Address decode



A link between pin 1 and 20 is only requisite if the memory card is to be used in a Nascom 1 system.

fig.8 Suggested link options.



11. References

- 1. Z80 CPU Technical manual
- 2. Nasbus functional specification. Issue 7.
- 3. MOSTEK MK4116 RAM data sheet
- 4. Nascom 1 constructional notes
- 5. Nascom 2 constructional notes
- 6. Nascom Buffer card specification.
- 7. MOSTEK Z80 Dynamic RAM interface application note.

This documentation was prepared on the NAS-PEN Text proccessor.

